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(54) **SEMICONDUCTOR ELEMENT**

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(52) **U.S. Cl.** **D13/182**

(58) **Field of Search** D13/182; D14/172,
D14/212, 233; 117/95; 216/227; 257/146,
618; 313/309, 310, 327, 336; 369/112.08,
112.09; 438/460

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(57) **CLAIM**

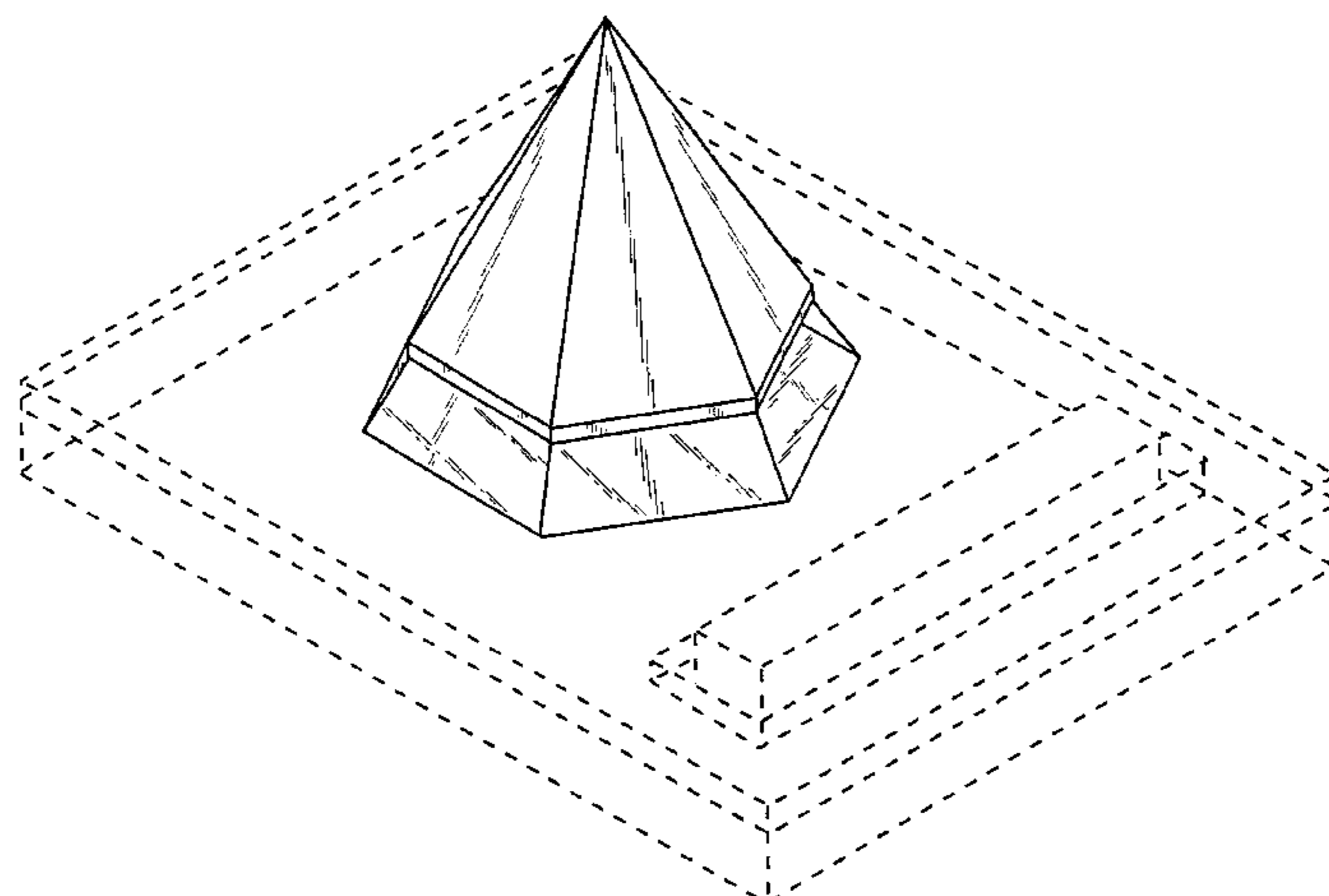
The ornamental design for a semiconductor element, as shown and described.

DESCRIPTION

FIG. 1 is front perspective of a semiconductor element showing our new design, wherein the truncated hexagonal pyramid portion thereof is transparent; FIG. 2 is a front elevational view thereof; FIG. 3 is a rear elevational view thereof; FIG. 4 is a right side elevational view thereof; FIG. 5 is a left side elevational view thereof; and, FIG. 6 is a top plan view thereof.

Portions in broken lines are for illustrative purposes only and form no part of claimed design.

1 Claim, 4 Drawing Sheets



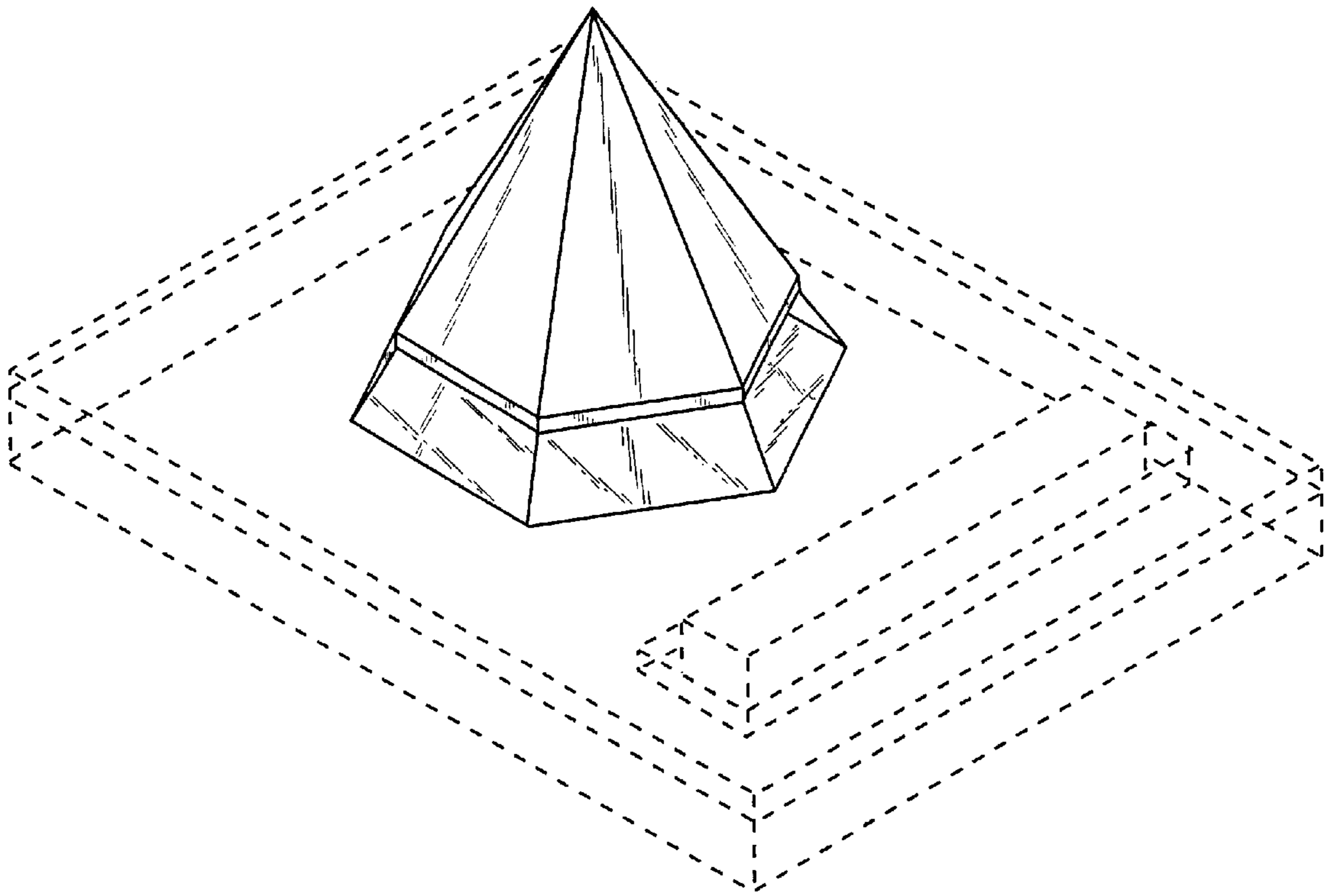


Fig. 1

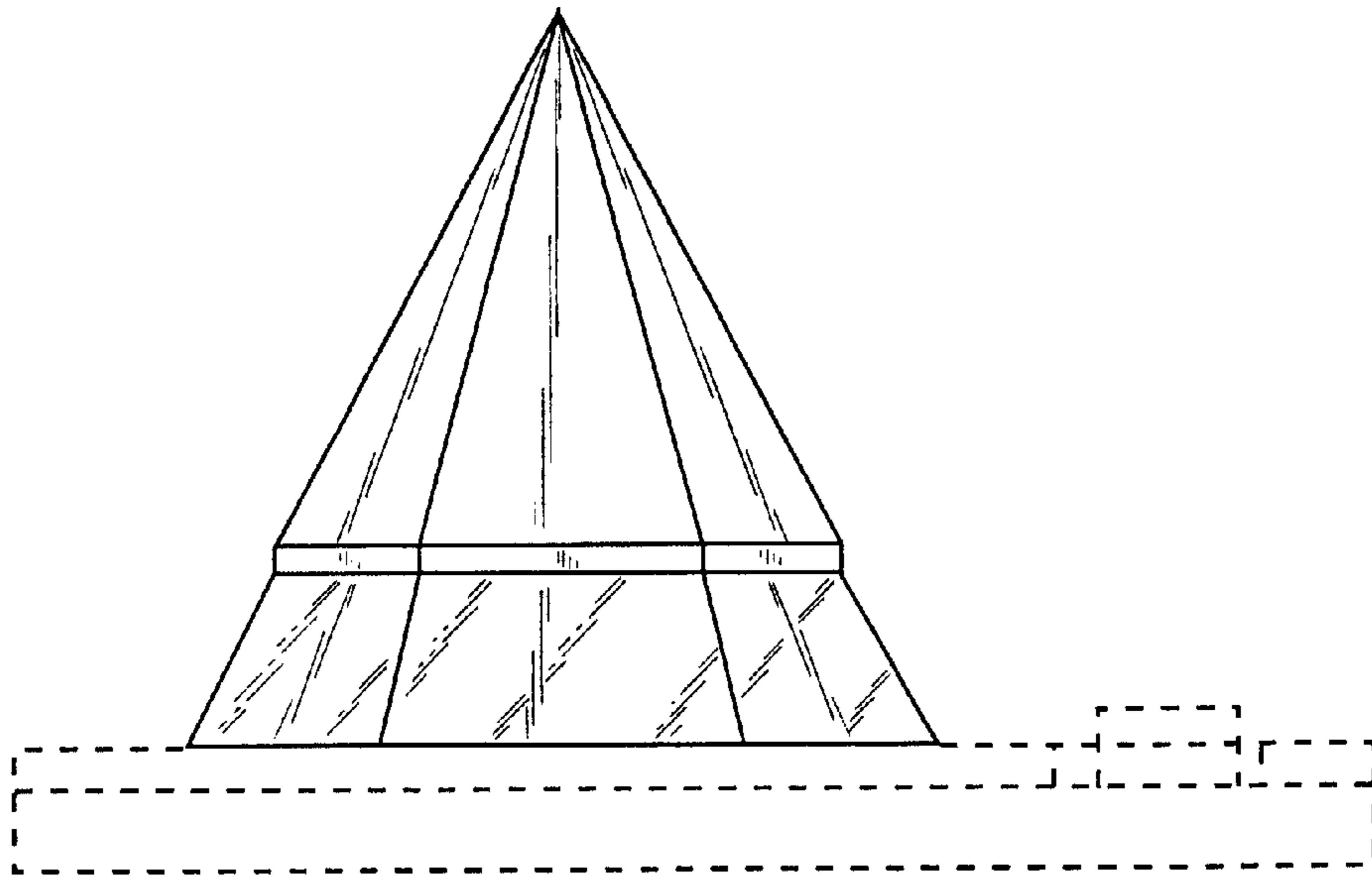


Fig. 2

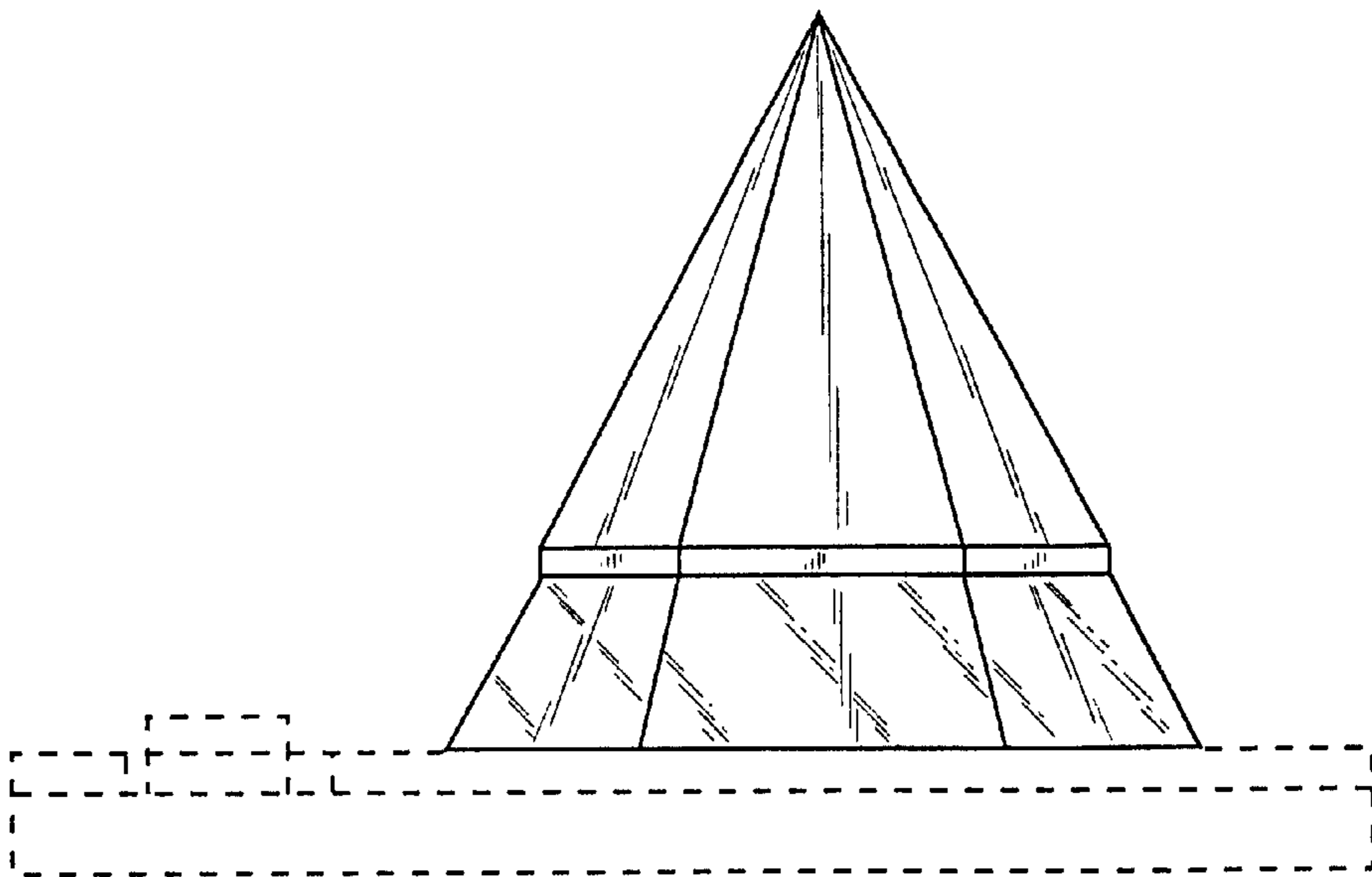


Fig. 3

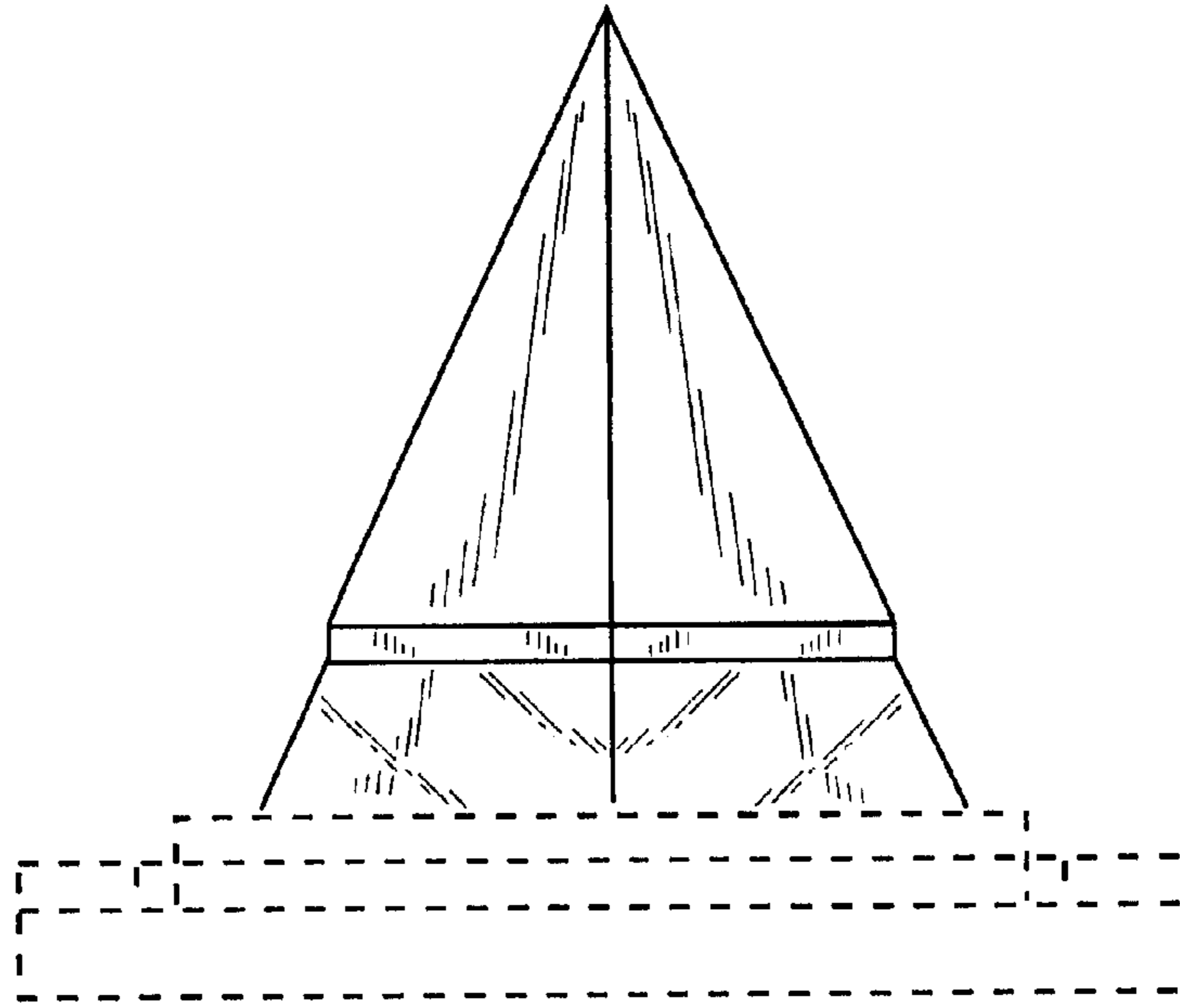


Fig. 4

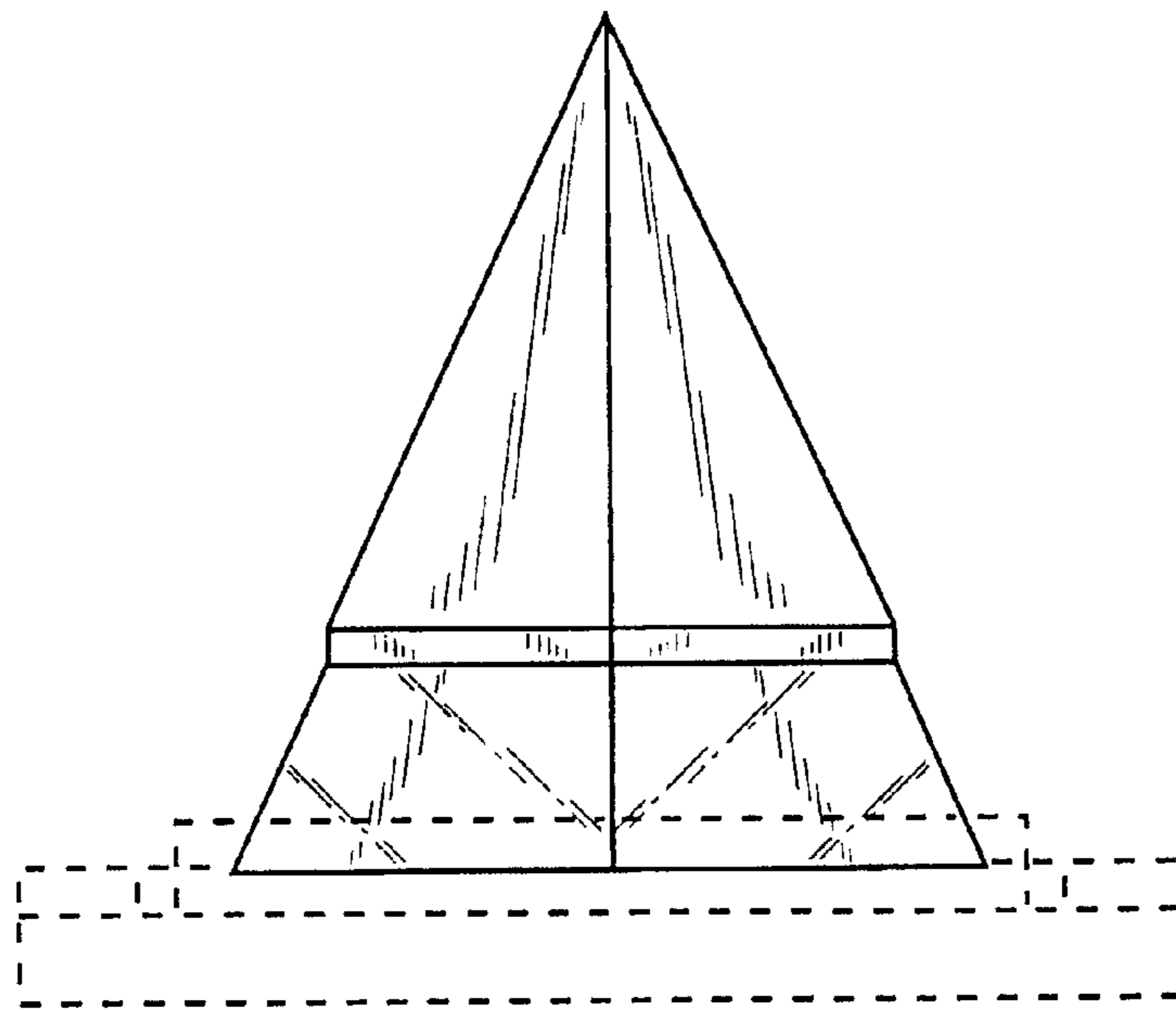


Fig. 5

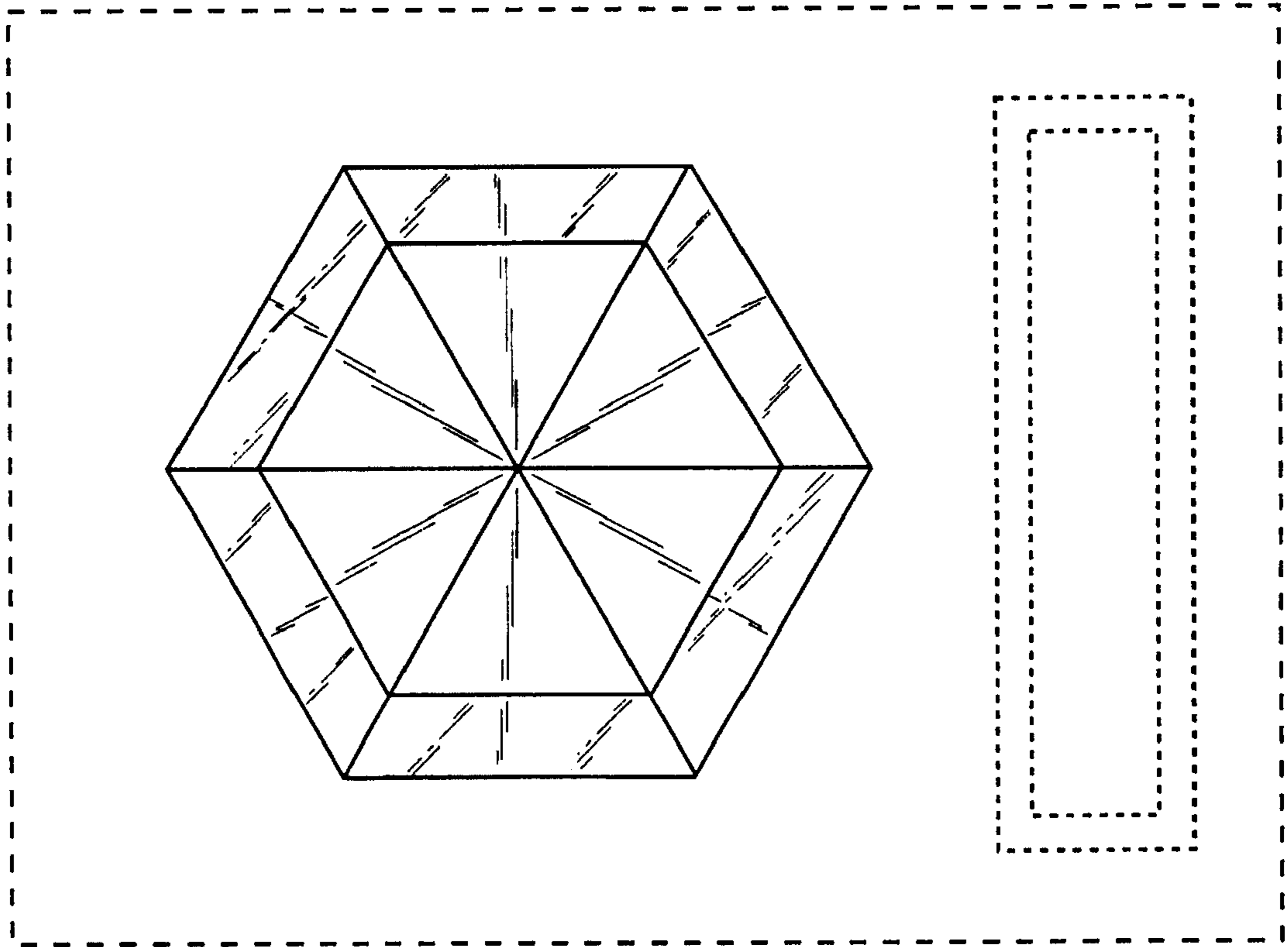


Fig. 6